



UNISONIC TECHNOLOGIES CO., LTD

02P35Z

POWER MOSFET

200mA, 350V P-CHANNEL POWER MOSFET

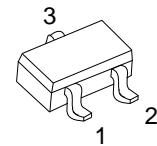
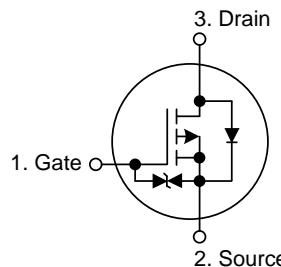
■ DESCRIPTION

The UTC **02P35Z** is a silicon P-channel MOSFET, it uses UTC's advanced technology to provide the customers with a minimum on state resistance, high switching speed and low gate charge.

■ FEATURES

- * $R_{DS(ON)} \leq 15\Omega$ @ $V_{GS}=-10V$, $I_D=-0.1A$
- * $R_{DS(ON)} \leq 16.5\Omega$ @ $V_{GS}=-4.5V$, $I_D=-0.1A$
- * High switching speed
- * Low input capacitance

■ SYMBOL



SOT-23
(EIAJ SC-59)

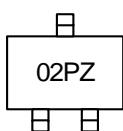
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
02P35ZL-AE3-R	02P35ZG-AE3-R	SOT-23	G	S	D	Tape Reel

Note: Pin Assignment: G: Gate S: Source D: Drain

02P35ZG-AE3-R	(1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) AE3: SOT-23 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ ABSOLUTE MAXIMUM RATING ($T_c=25^\circ\text{C}$ unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	-350	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	-0.2	A
	Pulsed (Note 2)	I_{DM}	-0.4	A
Power Dissipation		P_D	0.3	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature Range		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	350	$^\circ\text{C}/\text{W}$

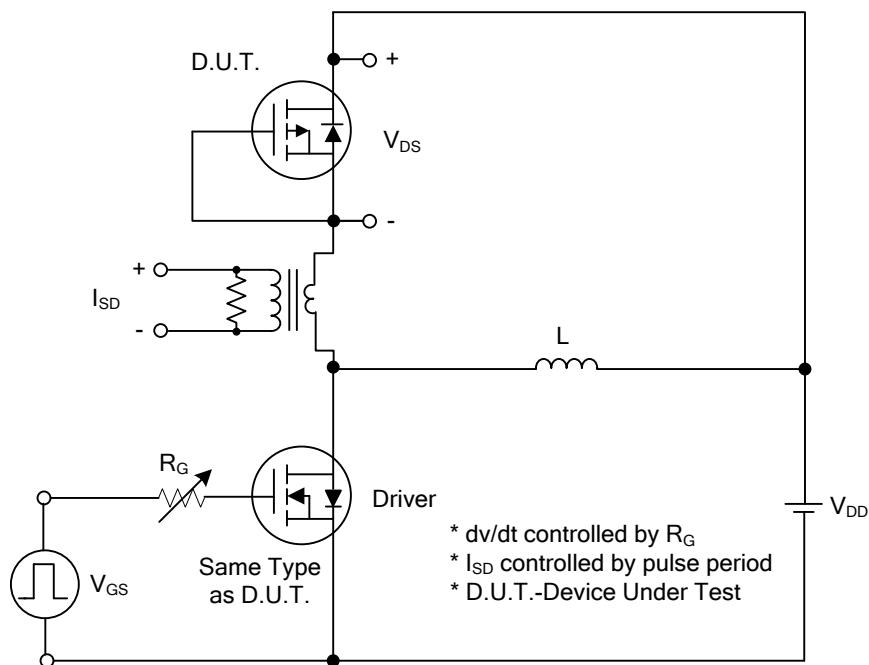
■ ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{V}, I_D=-250\mu\text{A}$	-350			V
Drain-Source Leakage Current	I_{DS}	$V_{DS}=-350\text{V}, V_{GS}=0\text{V}$			-10	μA
Gate-Source Leakage Current	Forward	$V_{GS}=+20\text{V}, V_{DS}=0\text{V}$			+10	μA
	Reverse	$V_{GS}=-20\text{V}, V_{DS}=0\text{V}$			-10	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(\text{TH})}$	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-1.0		-2.5	V
Static Drain-Source On-State Resistance	$R_{DS(\text{ON})}$	$V_{GS}=-10\text{V}, I_D=-0.1\text{A}$			15	Ω
		$V_{GS}=-4.5\text{V}, I_D=-0.1\text{A}$			16.5	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}, V_{DS}=-25\text{V}, f=1.0\text{MHz}$		77		pF
Output Capacitance	C_{OSS}			17.7		pF
Reverse Transfer Capacitance	C_{RSS}			4		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{DS}=-280\text{V}, V_{GS}=-10\text{V}, I_D=-200\text{mA}, I_G=-1\text{mA}$ (Note 1, 2)		8.4		nC
Gate to Source Charge	Q_{GS}			1.92		nC
Gate to Drain Charge	Q_{GD}			0.9		nC
Turn-ON Delay Time	$t_{D(\text{ON})}$	$V_{DD}=-100\text{V}, V_{GS}=-10\text{V}, I_D=-200\text{mA}, R_G=25\Omega$ (Note 1, 2)		3.2		ns
Rise Time	t_R			17.3		ns
Turn-OFF Delay Time	$t_{D(\text{OFF})}$			22.4		ns
Fall-Time	t_F			43.9		ns
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				-1	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				-2	A
Diode Forward Voltage	V_{SD}	$I_F=-0.2\text{A}, V_{GS}=0\text{V}$			-1.4	V

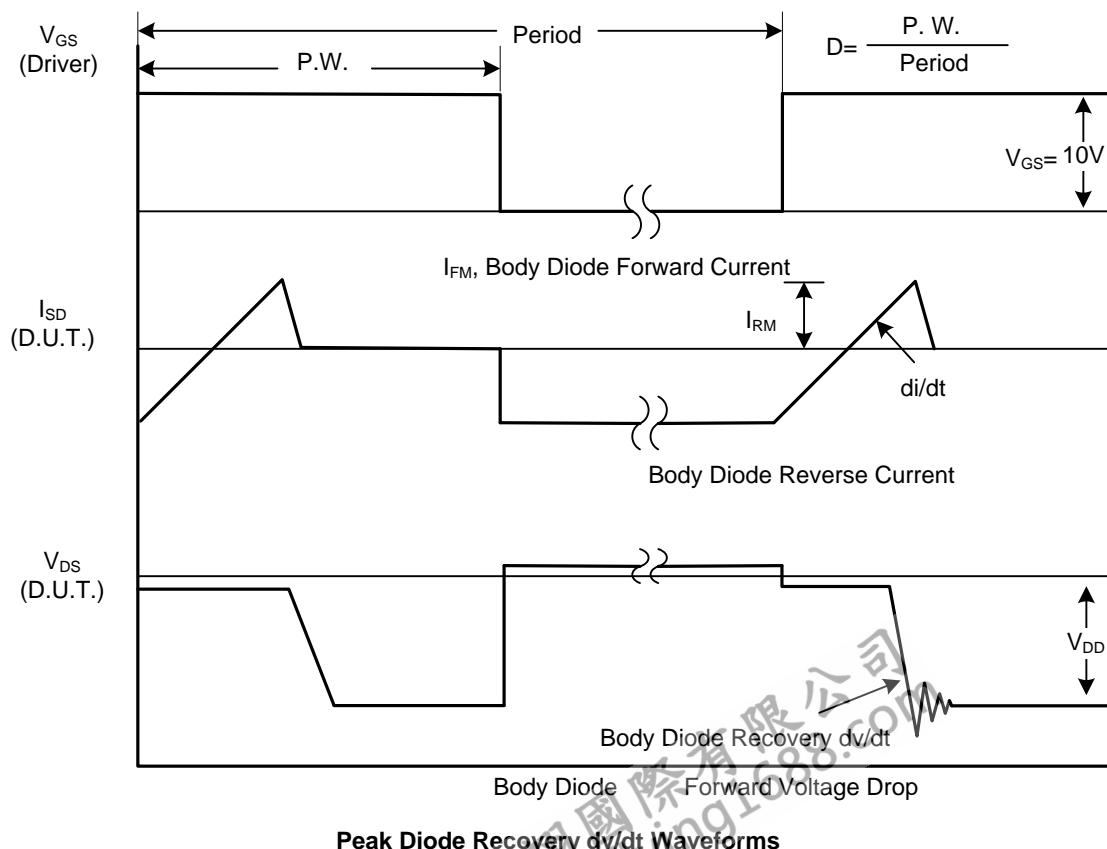
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

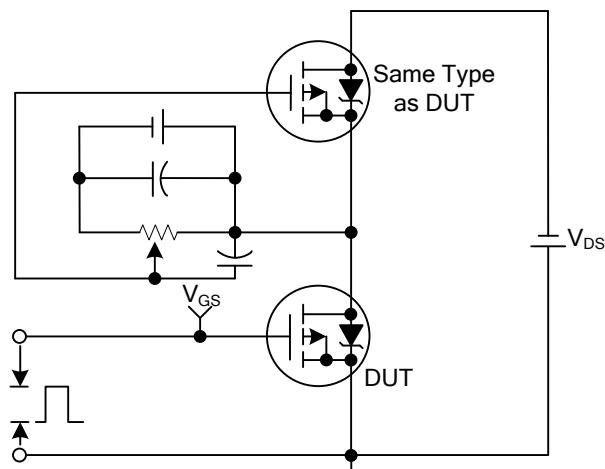


Peak Diode Recovery dv/dt Test Circuit

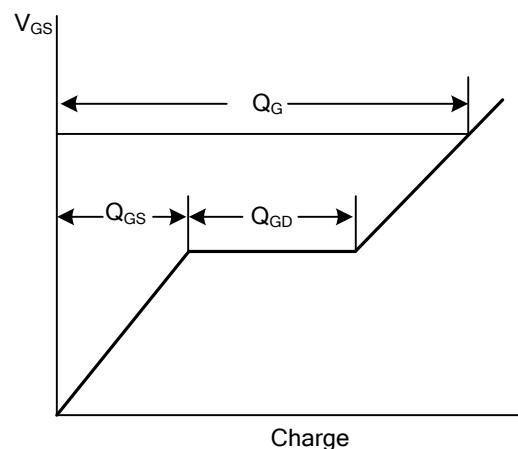


Peak Diode Recovery dv/dt Waveforms

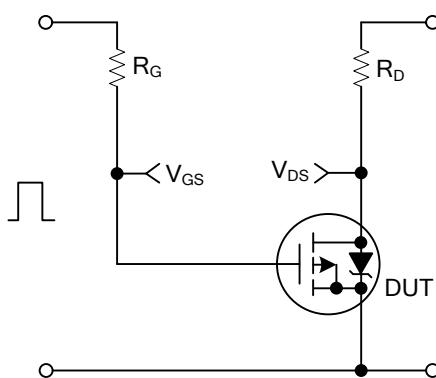
■ TEST CIRCUITS AND WAVEFORMS



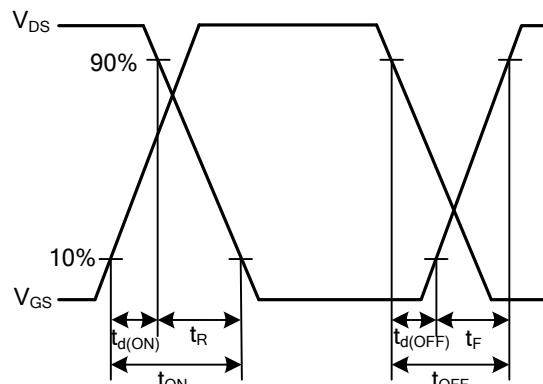
Gate Charge Test Circuit



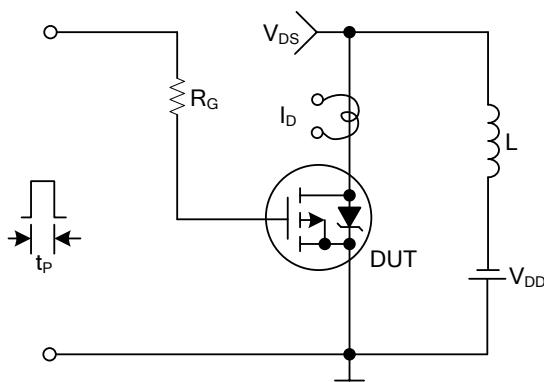
Gate Charge Waveforms



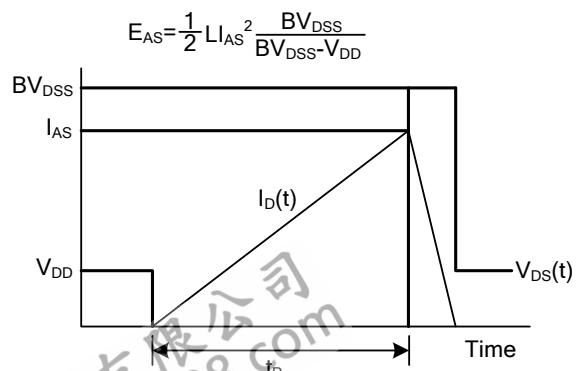
Resistive Switching Test Circuit



Resistive Switching Waveforms

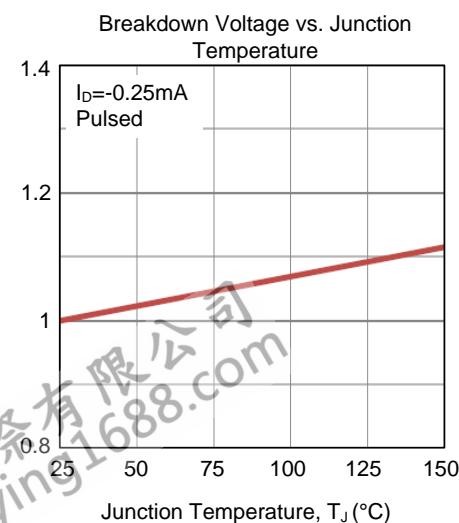
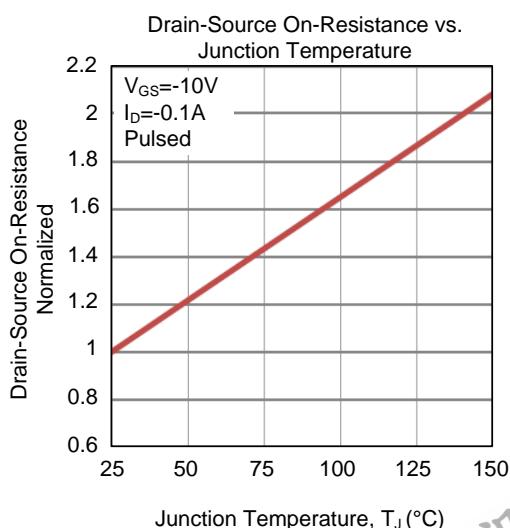
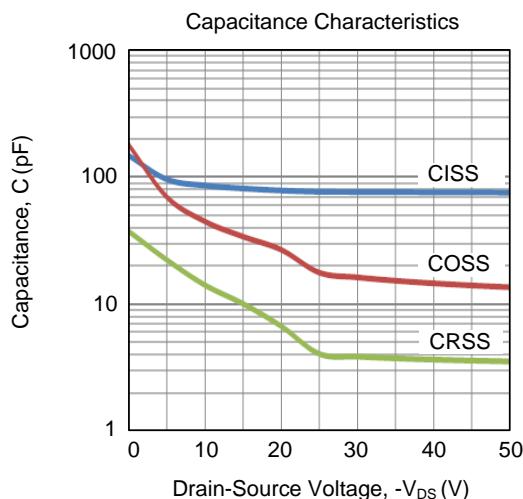
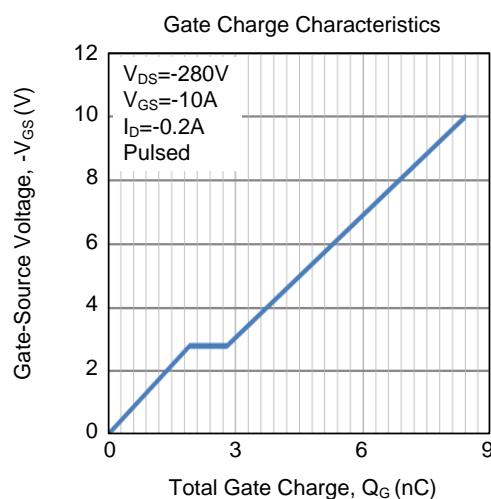
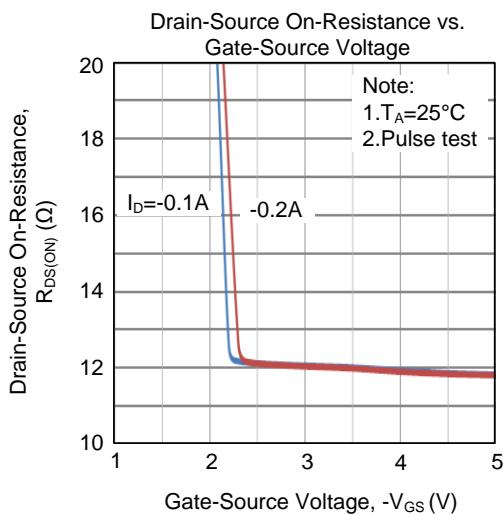
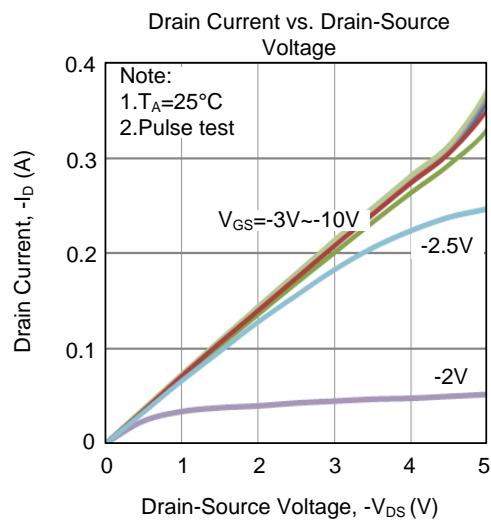


Unclamped Inductive Switching Test Circuit

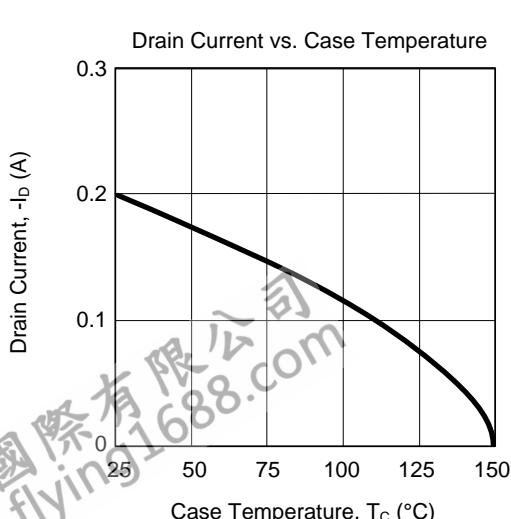
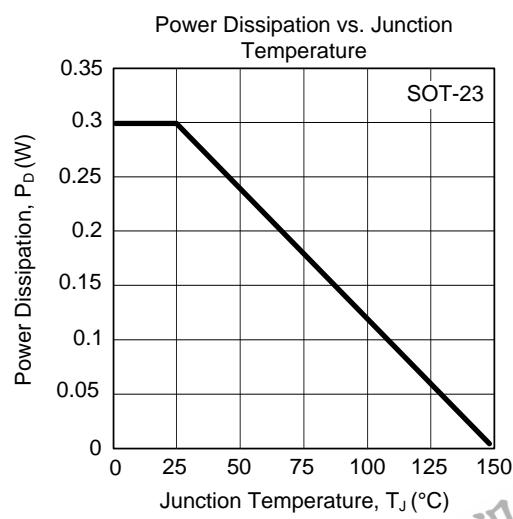
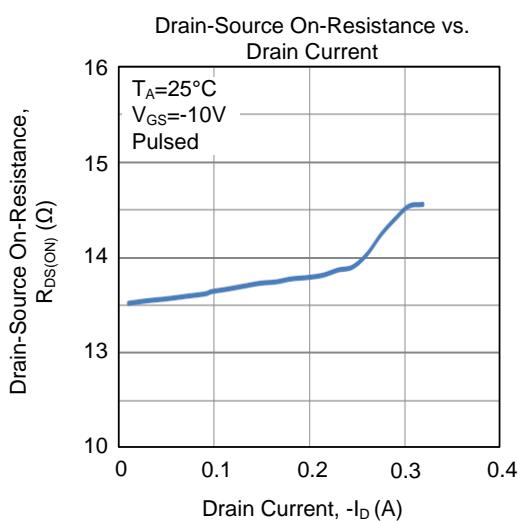
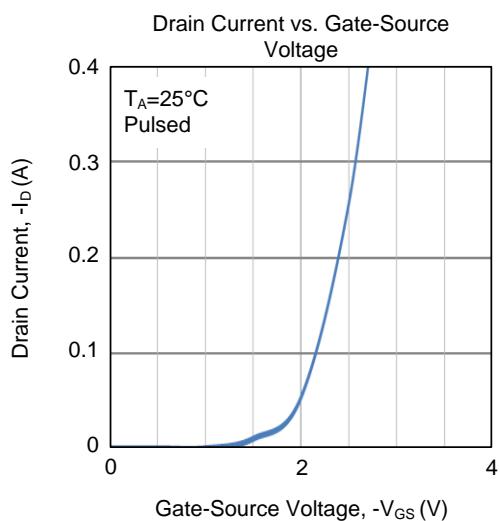
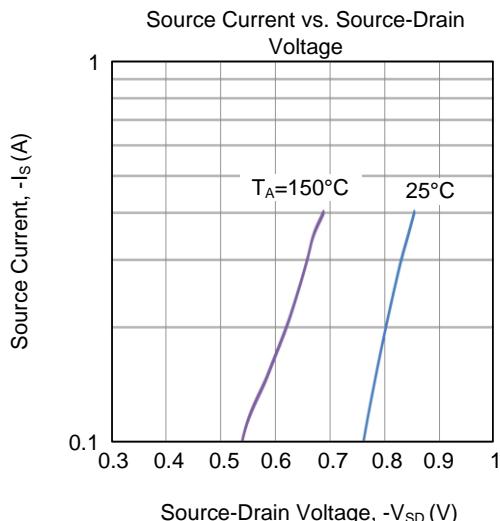
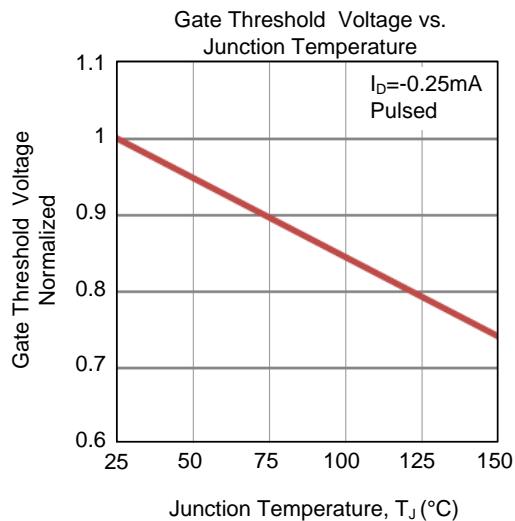


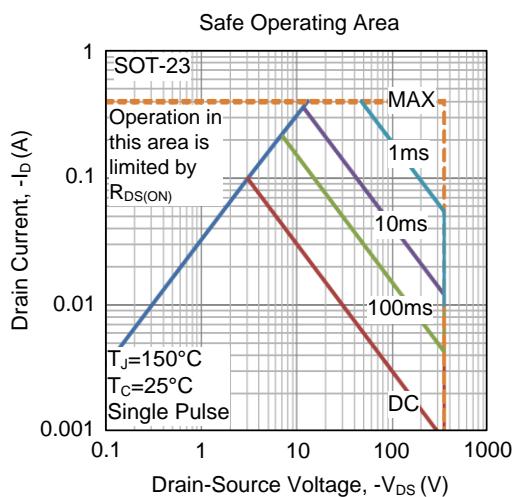
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)

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